TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL IGBT

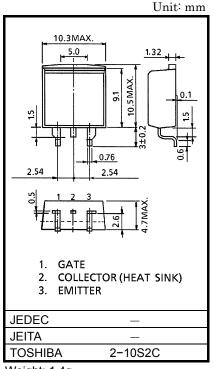
GT25G101(SM)

STROBE FLASH APPLICATIONS

- High Input Impedance
- Low Saturation Voltage : $V_{CE (sat)} = 8V (Max.) (I_C = 170A)$
- Enhancement-Mode
- 12V Gate Drive

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT | |
|---------------------------|-----------|------------------|---------|------|--|
| Collector-Emitter Voltage | | V _{CES} | 400 | V | |
| Gate-Emitter Voltage | | V _{GES} | ±25 | V | |
| Collector Current | DC | IC | 25 | А | |
| Collector Current | 1ms | I _{CP} | 170 | | |
| Collector Power | Ta = 25°C | PC | 1.3 | W | |
| Dissipation | Tc = 25°C | PC | 75 | VV | |
| Junction Temperature | | Tj | 150 | °C | |
| Storage Temperature Range | | T _{stg} | -55~150 | °C | |



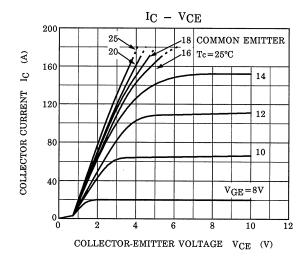
Weight: 1.4g

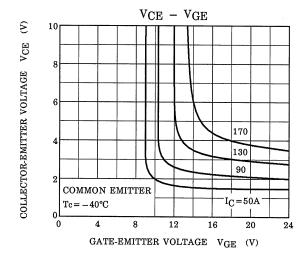
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

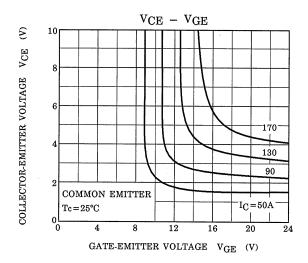
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

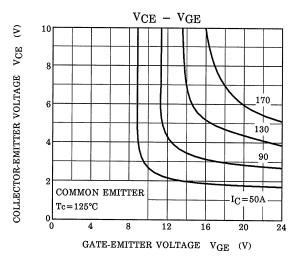
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

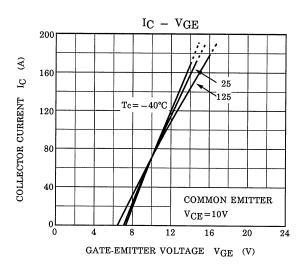
| CHARAG | CTERISTIC | SYMBOL | TEST CONDITION | MIN | TYP. | MAX | UNIT |
|--|--------------------|-----------------------|--|------|------|------|------|
| Gate Leakage Cu | rrent | I _{GES} | V _{GE} = ±25V, V _{CE} = 0 | _ | _ | ±100 | nA |
| Collector Cut-off | Current | I _{CES} | V _{CE} = 400V, V _{GE} = 0 | - | _ | 10 | μΑ |
| Gate-Emitter Cut | −off Voltage | V _{GE} (OFF) | I _C = 1mA, V _{CE} = 5V | 4 | 5 | 7 | V |
| Collector-Emitter | Saturation Voltage | V _{CE (sat)} | I _C = 170A, V _{GE} = 20V (Pulsed) | _ | 5 | 8 | V |
| Input Capacitance | | C _{ies} | V _{CE} = 10V, V _{GE} = 0, f = 1MHz | _ | 2000 | _ | pF |
| Switching Time | Rise Time | t _r | $\begin{array}{c c} 20V & 51\Omega & & \\ \hline 0 & 51\Omega & & \\ \hline V_{IN}: t_r \leq 100 ns & & \\ t_f \leq 100 ns & & 300V \\ \hline Duty cycle \leq 1\% & & \end{array}$ | _ | 0.1 | 0.5 | - µs |
| | Turn-on Time | t _{on} | | _ | 0.15 | 0.5 | |
| | Fall Time | t _f | | _ | 4.0 | 6.0 | |
| | Turn-off Time | t _{off} | | - | 4.5 | 7.0 | |
| Thermal Resistance R _{th (j-c)} — | | - | _ | 1.66 | °C/W | | |

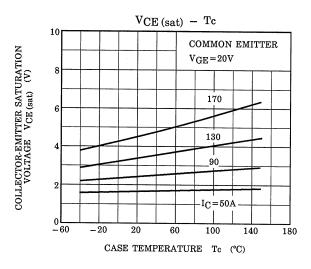


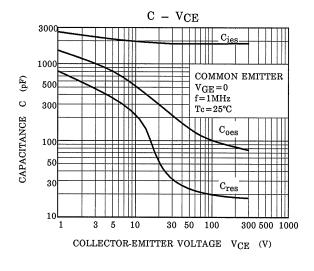


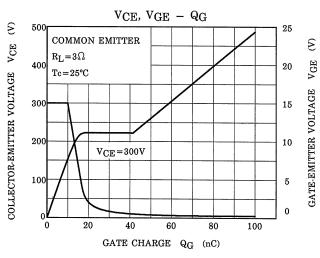


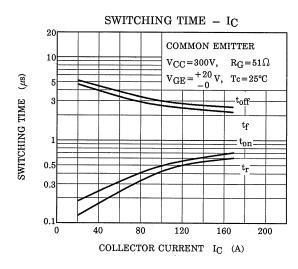


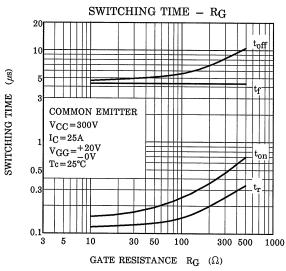


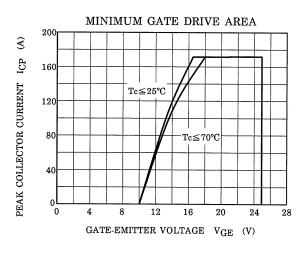


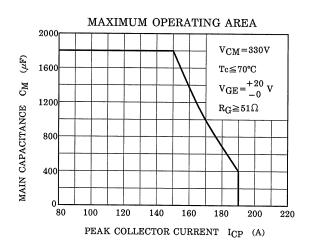












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